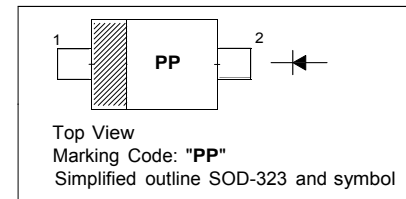


## SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

For super-high speed switching and wave detection circuit applications

### PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | Cathode     |
| 2   | Anode       |



### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

| Parameter                 | Symbol    | Value         | Unit             |
|---------------------------|-----------|---------------|------------------|
| Peak Reverse Voltage      | $V_{RM}$  | 30            | V                |
| Reverse Voltage           | $V_R$     | 30            | V                |
| Forward Current           | $I_F$     | 30            | mA               |
| Peak Forward Current      | $I_{FM}$  | 150           | mA               |
| Junction Temperature      | $T_j$     | 125           | $^\circ\text{C}$ |
| Storage Temperature Range | $T_{stg}$ | - 55 to + 125 | $^\circ\text{C}$ |

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter   | Symbol   | Typ.   | Max.     | Unit          |
|---|----------|--------|----------|---------------|
| Forward Voltage<br>at $I_F = 1\text{ mA}$<br>at $I_F = 30\text{ mA}$  | $V_F$    | -<br>- | 0.4<br>1 | V             |
| Reverse Current<br>at $V_R = 30\text{ V}$   | $I_R$    | -      | 0.3      | $\mu\text{A}$ |
| Terminal Capacitance<br>at $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$  | $C_T$    | 1.5    | -        | pF            |
| Reverse Recovery Time<br>at $I_F = I_R = 10\text{ mA}$ , $I_{rr} = 1\text{ mA}$ , $R_L = 100\ \Omega$                               | $t_{rr}$ | 1      | -        | ns            |
| Detection Efficiency<br>at $V_{in} = 3\text{ V}_{(peak)}$ , $f = 30\text{ MHz}$ , $R_L = 3.9\text{ K}\Omega$ , $C_L = 10\text{ pF}$ | $\eta$   | 65     | -        | %             |



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